

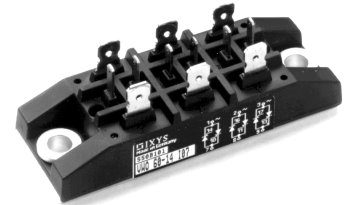
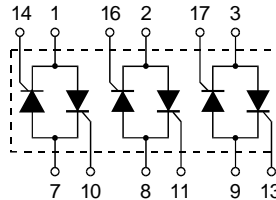
Three Phase AC Controller Modules

$$I_{RMS} = 3 \times 39 \text{ A}$$

$$V_{RRM} = 800-1600 \text{ V}$$

Preliminary data

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
800	800	VWO 36-08io7
1200	1200	VWO 36-12io7
1400	1400	VWO 36-14io7
1600	1600	VWO 36-16io7



Symbol	Test Conditions	Maximum Ratings
I_{RMS}	$T_K = 85^\circ\text{C}$, 50 - 400 Hz (per phase)	39 A
I_{TRMS}	$T_{VJ} = T_{VJM}$	28 A
I_{TAVM}	$T_K = 85^\circ\text{C}$; (180° sine)	18 A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	t = 10 ms (50 Hz), sine 320 A t = 8.3 ms (60 Hz), sine 350 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine 280 A t = 8.3 ms (60 Hz), sine 310 A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	t = 10 ms (50 Hz), sine 500 A ² s t = 8.3 ms (60 Hz), sine 520 A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine 390 A ² s t = 8.3 ms (60 Hz), sine 400 A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ f = 50 Hz, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$ $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	repetitive, $I_T = 20 \text{ A}$ 150 A/ μs
	$T_{VJ} = T_{VJM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$ 500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	1000 V/ μs
	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$ 10 W $t_p = 300 \mu\text{s}$ 5 W
P_{GAVM}		0.5 W
V_{RGM}		10 V
T_{VJ}		-40...+125 °C
T_{VJM}		125 °C
T_{stg}		-40...+125 °C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	t = 1 min 2500 V~ t = 1 s 3000 V~
	M_d	Mounting torque (M5) (10-32 UNF)
Weight	typ.	110 g

Features

- Thyristor controller for AC (circuit W3C acc. to IEC) for mains frequency
- Package with metal base plate
- Isolation voltage 3000 V~
- Planar passivated chips
- UL applied
- 1/4" fast-on power terminals

Applications

- Switching and control of three phase AC circuits
- Softstart AC motor controller
- Solid state switches
- Light and temperature control

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density
- Light weight and compact

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.
IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values	
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	\leq	5 mA
V_T	$I_T = 45 \text{ A}; T_{VJ} = 25^\circ\text{C}$	\leq	1.45 V
V_{T0}	For power-loss calculations only		0.85 V
r_T			13 m Ω
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	1.0 V
	$T_{VJ} = -40^\circ\text{C}$	\leq	1.2 V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	65 mA
	$T_{VJ} = -40^\circ\text{C}$	\leq	80 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	\leq	0.2 V
I_{GD}		\leq	5 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	\leq	150 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	\leq	100 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	\leq	2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}, t_p = 200 \mu\text{s}; di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	150 μs
R_{thJC}	per thyristor; sine 180°el per module		1.3 K/W 0.216 K/W
R_{thJK}	per thyristor; sine 180°el per module		1.5 K/W 0.25 K/W
d_s	Creeping distance on surface		16.1 mm
d_A	Creepage distance in air		6.0 mm
a	Max. allowable acceleration		50 m/s ²

Dimensions in mm (1 mm = 0.0394")
